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ABSTRACT OF THE DISCLOSURE

THIN-FILM SEMICONDUCTOR EPITAXIAL SUBSTRATE AND
PROCESS FOR PRODUCTION THEREOF

A thin-film semiconductor epitaxial substrate comprising a substrate and a sub-collector layer, a collector layer, a base layer and an emitter layer(s) which are formed as thin-film semiconductor epitaxial layers on said substrate, wherein boron (B) added is present in at least a part of a layer portion comprising said sub-collector layer and said collector layer.

(Figure 1)